AMPLEON

Power LDMOS transistor
Rev. 4 — 7 September 2023

Product data sheet

Product profile 1.

1.1 General description

Based on Advanced Rugged Technology (ART), this 2000 W LDMOS RF power transistor has been designed to cover a wide range of applications for ISM, broadcast and communications. The unmatched transistor has a frequency range of 1 MHz to 450 MHz.

Table 1. **Application information**

Test signal	f	V _{DS}	PL	Gp	ηD
	(MHz)	(V)	(W)	(dB)	(%)
CW	41	65	1600	28.8	79.4
CW pulsed [1][2]	60	55	1250	24.7	85.8
CW pulsed [1][2]	60	65	1690	25.1	83.3
CW pulsed [1][2]	64	65	1785	25.7	84.7
CW [3]	87.5 to 108	60	1730	25.8	85.1

^[1] $t_p = 100 \ \mu s; \ \delta = 10 \ \%.$

1.2 Features and benefits

- High breakdown voltage enables class E operation up to V_{DS} = 53 V
- Qualified up to a maximum of V_{DS} = 65 V
- Characterized from 30 V to 65 V to support a wide range of applications
- Integrated dual sided ESD protection enables class C operation and complete switch off of the transistor
- Excellent ruggedness with no device degradation
- High efficiency
- Excellent thermal stability
- Designed for broadband operation
- For RoHS compliance see the product details on the Ampleon website

^[2] Performance at 3 dB gain compression level.

^[3] Center band performance numbers across the indicated frequency range.

1.3 Applications

- Industrial, scientific and medical applications
 - ◆ Plasma generators
 - ◆ MRI systems
 - ◆ Particle accelerators
- Broadcast
 - ◆ FM radio
 - VHF TV
- Communications
 - Non cellular communications
 - ◆ UHF radar

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
ART	2K0PE (OMP-1230-4F-	1)	
1	gate1		
2	gate2	4 3	
3	drain2		, 1
4	drain1		5
5	source		2—
		1 2	" "
			3 amp01358
ART	 2K0PEG (OMP-1230-40	G-1)	
1	gate1		
2	gate2	4 3	4
3	drain2	5	, [4
4	drain1	<u> </u>	5
5	source	1 2	2—
			<u>"</u>
			3 amp01358

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Package name	Orderable part number	12NC	Packing description	Min. orderable quantity (pieces)
OMP-1230-4F-1	ART2K0PEZ	9349 606 96517	Tray; 20-fold; dry pack	60
	ART2K0PEY	9349 606 96518	TR13; 100-fold; 56 mm; dry pack	100
OMP-1230-4G-1	ART2K0PEGZ	9349 606 97517	Tray; 20-fold; dry pack	60
	ART2K0PEGY	9349 606 97518	TR13; 100-fold; 56 mm; dry pack	100

ART2K0PE_ART2K0PEG

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	[1]	-	200	V
V_{GS}	gate-source voltage		-9	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[2]	-	225	°C

^[1] Specified over lifetime at maximum operating temperature.

5. Thermal characteristics

Table 5. Thermal characteristics

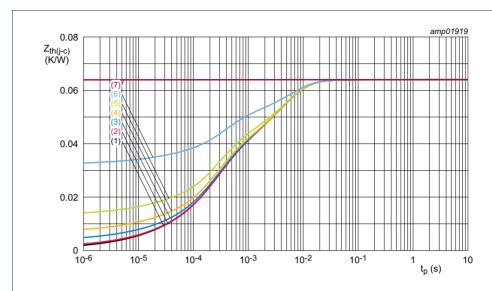
According to standard MIL-STD-883E.

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_j = 95$ °C, measured under RF condition	0.064	K/W

^[1] Refer to application note AN221014 on the Ampleon website.

^[2] Continuous use at maximum temperature will affect the reliability.

^[2] See Figure 1.



- (1) $\delta = 0.1 \%$ (single push)
- (2) $\delta = 1 \%$
- (3) $\delta = 5 \%$
- (4) $\delta = 10 \%$
- (5) $\delta = 20 \%$
- (6) $\delta = 50 \%$
- (7) $\delta = 100 \%$ (steady state)

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

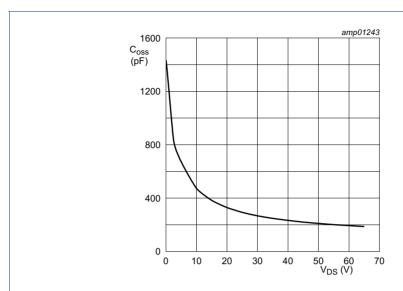
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 5.5 \text{ mA}$	203	208	-	V
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 20 \text{ V}; I_D = 550 \text{ mA}$	1.6	2.1	2.6	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 65 V	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 20 \text{ V}$	-	76	-	А
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	280	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 19.25 \text{ A}$	-	0.106	-	Ω

Table 7. AC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 65 \text{ V}; f = 1 \text{ MHz}$	-	3.27	-	pF
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 65 V; f = 1 MHz	-	614	-	pF
C _{oss}	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 65 \text{ V}; f = 1 \text{ MHz}$	-	187	-	pF

ART2K0PE_ART2K0PEG



 $V_{GS} = 0 V; f = 1 MHz$

Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

Table 8. RF characteristics

Test signal: pulsed RF; $t_p = 100~\mu s$; $\delta = 3~\%$; f = 108~MHz; RF performance at $V_{DS} = 65~V$; $I_{Dq} = 50~mA$ per section; $T_{case} = 25~^{\circ}C$; unless otherwise specified; in a class-AB production test circuit.

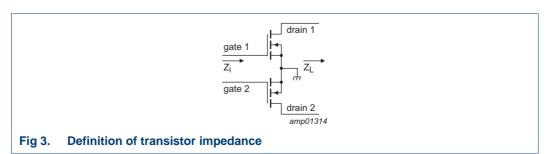
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G _p	power gain	P _L = 2000 W	26.5	27.7	-	dB
RLin	input return loss	P _L = 2000 W	-	-15	-	dB
η_{D}	drain efficiency	P _L = 2000 W	68.0	71.7	-	%

7. Test information

7.1 Ruggedness in class-AB operation

The ART2K0PE and ART2K0PEG are capable of withstanding a load mismatch corresponding to VSWR ≥ 65 : 1 through all phases under the following conditions: $V_{DS} = 65$ V; $I_{Dq} = 100$ mA per section; $P_L = 2000$ W pulsed; $t_p = 100$ $\mu s; \, \delta = 10$ %; f = 108 MHz.

7.2 Impedance information



ART2K0PE_ART2K0PEG

Table 9. Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at $V_{DS} = 65 \text{ V}$ and $P_L = 2000 \text{ W}$.

f	Z _i	Z_L
(MHz)	(Ω)	(Ω)
108	2.4 – j8.7	3.8 + j0.9

7.3 Test circuit

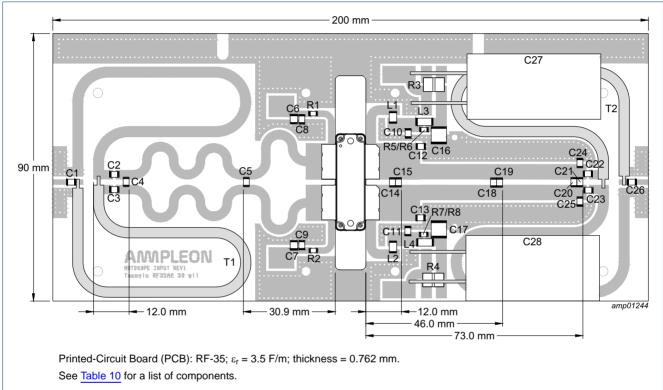


Fig 4. Component layout

Table 10. List of components

For test circuit see Figure 4.

Component	Description	Value		Remarks
C1, C26	multilayer ceramic chip capacitor	470 pF	[1]	
C2, C3	multilayer ceramic chip capacitor	68 pF	<u>[1]</u>	
C4	multilayer ceramic chip capacitor	43 pF	<u>[1]</u>	
C5	multilayer ceramic chip capacitor	300 pF	[1]	
C6, C7	multilayer ceramic chip capacitor	4.7 μF, 50 V		Murata: GRM32ER71H475KA88L
C8, C9, C10, C11	multilayer ceramic chip capacitor	920 pF	<u>[1]</u>	
C12, C13	multilayer ceramic chip capacitor	180 pF	<u>[1]</u>	
C14, C15	multilayer ceramic chip capacitor	39 pF	<u>[1]</u>	
C16, C17	multilayer ceramic chip capacitor	4.7 μF, 100 V		TDK: C5750X7R2A475KT/A
C18, C19	multilayer ceramic chip capacitor	56 pF	<u>[1]</u>	
C20, C21	multilayer ceramic chip capacitor	51 pF	[1]	

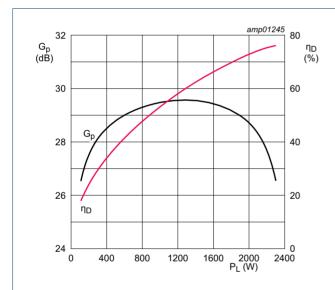
Table 10. List of components ... continued

For test circuit see Figure 4.

Component	Description	Value	Remarks
C22, C23	multilayer ceramic chip capacitor	120 pF [1]	
C24, C25	multilayer ceramic chip capacitor	20 pF [1]	
C27, C28	electrolytic capacitor	2200 μF, 100 V	
L1, L2	air inductor	47 nH	Coilcraft: 1515SQ-47N
L3, L4	air inductor	82 nH	Coilcraft: 1515SQ-82N
R1, R2	resistor	4.7 kΩ	SMD 1206
R3, R4	resistor	0.01 Ω	Vishay: WSHP2818
R5, R6, R7, R8	resistor	9.1 Ω	SMD 1206
T1, T2	semi rigid coax	50 Ω, 160 mm	EZ141-AL-TP/M17

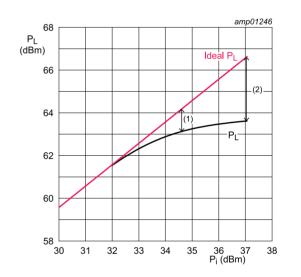
^[1] American Technical Ceramics type 100B or capacitor of same quality.

7.4 Graphical data



 V_{DS} = 65 V; I_{Dq} = 100 mA per section; f = 108 MHz; t_p = 100 μ s; δ = 10 %.

Fig 5. Power gain and drain efficiency as function of output power; typical values

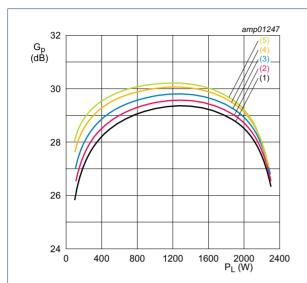


 V_{DS} = 65 V; I_{Dq} = 100 mA per section; f = 108 MHz; t_p = 100 $\mu s; \, \delta$ = 10 %.

- (1) $P_{L(1dB)} = 63.20 \text{ dBm } (2045 \text{ W})$
- (2) $P_{L(3dB)} = 63.71 \text{ dBm } (2300 \text{ W})$

Fig 6. Output power as a function of input power; typical values

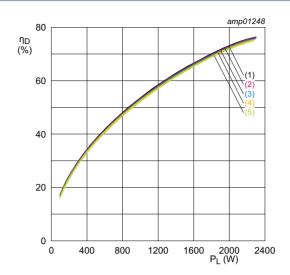
Power LDMOS transistor



 $V_{DS} = 65 \text{ V; } f = 108 \text{ MHz; } t_p = 100 \text{ } \mu\text{s; } \delta = 10 \text{ } \%.$

- (1) $I_{Dq} = 50 \text{ mA per section}$
- (2) $I_{Da} = 100 \text{ mA per section}$
- (3) $I_{Dq} = 200 \text{ mA per section}$
- (4) $I_{Dq} = 400 \text{ mA per section}$
- (5) $I_{Dq} = 600 \text{ mA per section}$

Fig 7. Power gain as a function of output power; typical values

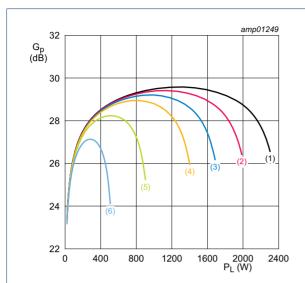


 V_{DS} = 65 V; f = 108 MHz; t_p = 100 $\mu s;$ δ = 10 %.

- (1) $I_{Dq} = 50 \text{ mA per section}$
- (2) $I_{Dq} = 100 \text{ mA per section}$
- (3) $I_{Dq} = 200 \text{ mA per section}$
- (4) $I_{Dq} = 400 \text{ mA per section}$
- (5) $I_{Dq} = 600 \text{ mA per section}$

Fig 8. Drain efficiency as a function of output power; typical values

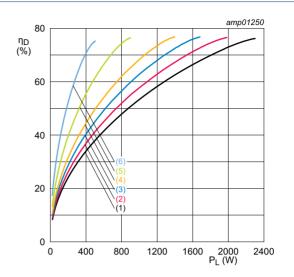
Power LDMOS transistor



 I_{Dq} = 100 mA per section; f = 108 MHz; t_p = 100 $\mu s;$ δ = 10 %.

- (1) $V_{DS} = 65 \text{ V}$
- (2) $V_{DS} = 60 \text{ V}$
- (3) $V_{DS} = 55 \text{ V}$
- (4) $V_{DS} = 50 \text{ V}$
- (5) $V_{DS} = 40 \text{ V}$
- (6) $V_{DS} = 30 \text{ V}$

Fig 9. Power gain as a function of output power; typical values



 I_{Dq} = 100 mA per section; f = 108 MHz; t_p = 100 $\mu s;$ δ = 10 %.

- (1) $V_{DS} = 65 \text{ V}$
- (2) $V_{DS} = 60 \text{ V}$
- (3) $V_{DS} = 55 \text{ V}$
- (4) $V_{DS} = 50 \text{ V}$
- (5) $V_{DS} = 40 \text{ V}$
- (6) $V_{DS} = 30 \text{ V}$

Fig 10. Drain efficiency as a function of output power; typical values

8. Package outline

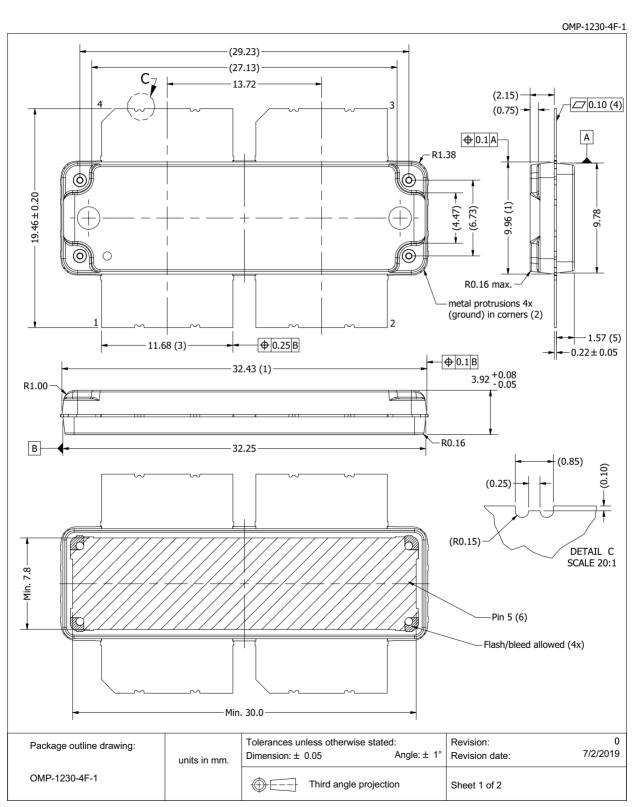
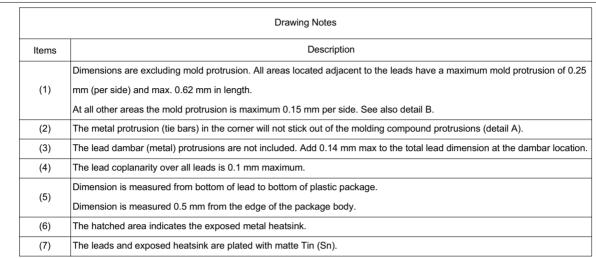


Fig 11. Package outline OMP-1230-4F-1 (sheet 1 of 2)

OMP-1230-4F-1



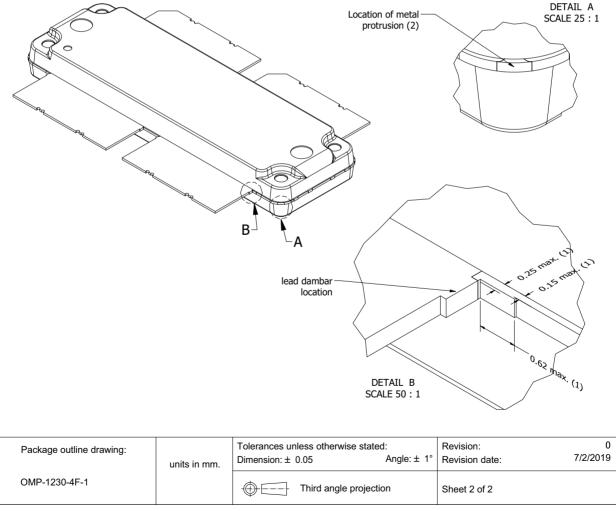


Fig 12. Package outline OMP-1230-4F-1 (sheet 2 of 2)

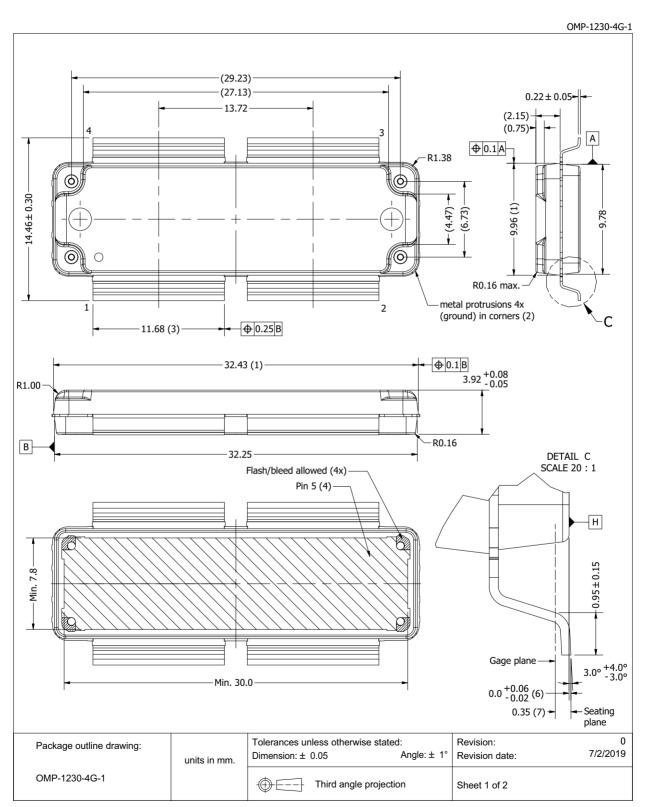


Fig 13. Package outline OMP-1230-4G-1 (sheet 1 of 2)

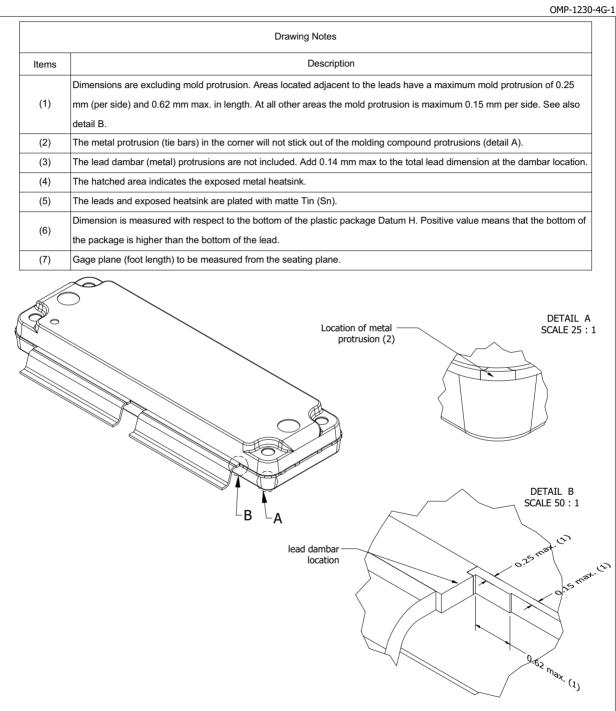


Fig 14. Package outline OMP-1230-4G-1 (sheet 2 of 2)

units in mm.

Tolerances unless otherwise stated:

Third angle projection

Dimension: ± 0.05

Revision:

Revision date:

Sheet 2 of 2

Angle: ± 1°

Package outline drawing:

OMP-1230-4G-1

0

7/2/2019

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

10. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
FM	Frequency Modulation
ISM	Industrial, Scientific and Medical
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MRI	Magnetic Resonance Imaging
RoHS	Restriction of Hazardous Substances
SMD	Surface Mounted Device
UHF	Ultra High Frequency
VHF	Very High Frequency
VSWR	Voltage Standing Wave Ratio

11. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
ART2K0PE_ART2K0PEG v.4	20230907	Product data sheet	-	ART2K0PE_ART2K0PEG v.3	
Modifications:	Section 1.1 on page 1: updated text of paragraph				
	Section 1.2 on page 1: updated				
	Section 1.3	on page 2: updated			
	• Table 3 on	page 2: updated 12NCs			
	• Table 4 on	page 3: updated			
	• Table note	2 on page 3: updated			
	• Table 5 on	page 3: updated			
	• Figure 1 on page 4: updated				
	• <u>Table 6 on page 4</u> : updated				
	• Table 8 on	page 5: updated			
	Section 7 o	n page 5: section 'Applic	ation information' i	removed	
ART2K0PE_ART2K0PEG v.3	20201019	Product data sheet	-	ART2K0PE v.2	
ART2K0PE v.2	20200806	Product data sheet	-	ART2K0PE_ART2K0PEG v.1	
ART2K0PE_ART2K0PEG v.1	20200114	Objective data sheet	-	-	

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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13. Contact information

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

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ART2K0PE; ART2K0PEG

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